

74LVC4066

Quad bilateral switch

Rev. 02 — 27 August 2007

Product data sheet

1. General description

The 74LVC4066 is a high-speed Si-gate CMOS device.

The 74LVC4066 provides four single pole, single-throw analog switch functions. Each switch has two input/output terminals (nY and nZ) and an active HIGH enable input (nE). When nE is LOW, the analog switch is turned off.

Schmitt-trigger action at the enable inputs makes the circuit tolerant of slower input rise and fall times across the entire V_{CC} range from 1.65 V to 5.5 V.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
 - ◆ 7.5 Ω (typical) at $V_{CC} = 2.7$ V
 - ◆ 6.5 Ω (typical) at $V_{CC} = 3.3$ V
 - ◆ 6 Ω (typical) at $V_{CC} = 5$ V
- Switch current capability of 32 mA
- High noise immunity
- CMOS low-power consumption
- Direct interface TTL-levels
- Latch-up performance exceeds 250 mA
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Enable inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74LVC4066D	-40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LVC4066PW	-40 °C to +125 °C	TSSOP14	plastic thin small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LVC4066BQ	-40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

4. Functional diagram

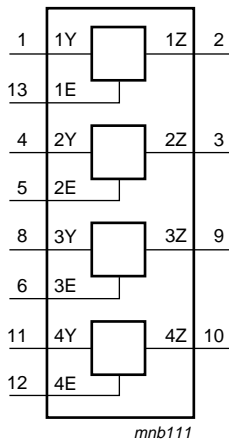


Fig 1. Logic symbol

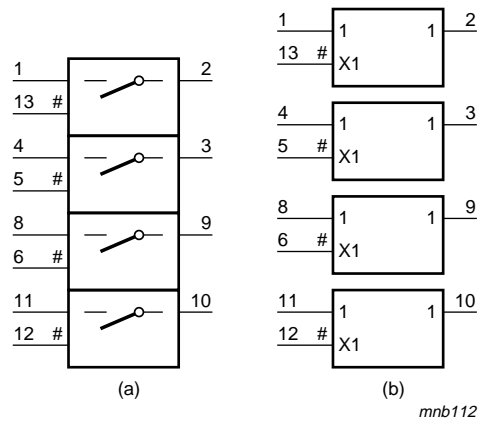


Fig 2. Logic symbol (IEEE/IEC)

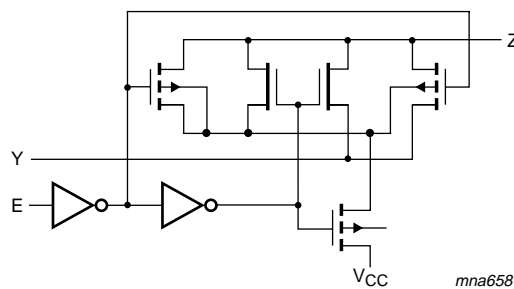
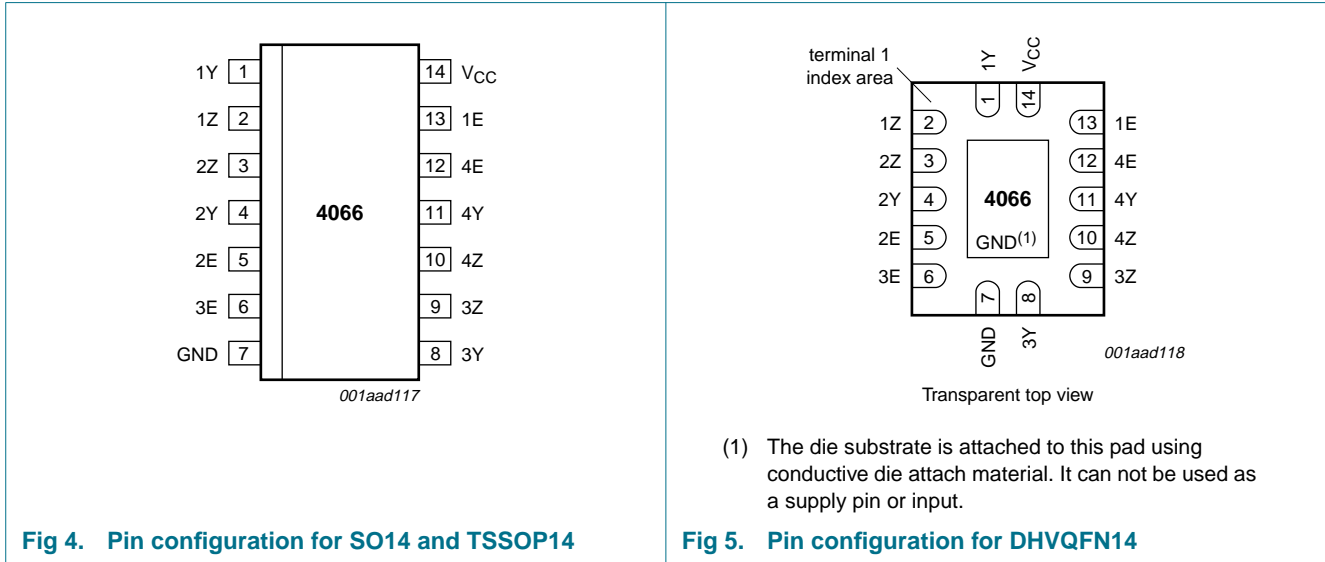


Fig 3. Logic diagram (one switch)

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1Y	1	independent input/output
1Z	2	independent output/input
2Z	3	independent output/input
2Y	4	independent input/output
2E	5	enable input (active HIGH)
3E	6	enable input (active HIGH)
GND	7	ground (0 V)
3Y	8	independent input/output
3Z	9	independent output/input
4Z	10	independent output/input
4Y	11	independent input/output
4E	12	enable input (active HIGH)
1E	13	enable input (active HIGH)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Input nE	Switch
L	OFF
H	ON

[1] H = HIGH voltage level;
L = LOW voltage level.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
V_I	input voltage		^[1] -0.5	+6.5	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I < V_{CC} + 0.5\text{ V}$	-50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5\text{ V}$ or $V_I < V_{CC} + 0.5\text{ V}$	-	±50	mA
V_{SW}	switch voltage	enable and disable mode	^[2] -0.5	+6.5	V
I_{SW}	switch current	$-0.5 < V_{SW} < V_{CC} + 0.5\text{ V}$	-	±50	mA
I_{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$	^[3] -	500	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] For SO14 packages: above 70 °C derate linearly with 8 mW/K.
For (T)SSOP14 packages: above 60 °C derate linearly with 5.5 mW/K.
For DHVQFN14 packages: above 60 °C derate linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_{SW}	switch voltage		[1] 0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65\text{ V to }2.7\text{ V}$	[2] -	-	20	ns/V
		$V_{CC} = 2.7\text{ V to }5.5\text{ V}$	[2] -	-	10	ns/V

[1] To avoid sinking GND current from terminal nZ when switch current flows in terminal nY, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no GND current will flow from terminal nY. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	$0.65V_{CC}$	-	-	$0.65V_{CC}$	-	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.7	-	-	1.7	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	2.0	-	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	-	$0.35V_{CC}$	-	$0.35V_{CC}$	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	-	0.7	-	0.7	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.8	-	0.8	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
I_I	input leakage current	pin nE; $V_{CC} = 5.5\text{ V}$; $V_I = 5.5\text{ V or GND}$	[2] -	± 0.1	± 5	-	± 20	μA
$I_{S(OFF)}$	OFF-state leakage current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5\text{ V}$; see Figure 6	[2] -	± 0.1	± 5	-	± 20	μA
$I_{S(ON)}$	ON-state leakage current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5\text{ V}$; see Figure 7	[2] -	± 0.1	± 5	-	± 20	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{SW} = \text{GND or } V_{CC}$; $V_{CC} = 5.5\text{ V}$; $I_O = 0\text{ A}$;	[2] -	0.1	10	-	40	μA
ΔI_{CC}	additional supply current	pin nE; $V_I = V_{CC} - 0.6\text{ V}$; $V_{CC} = 5.5\text{ V}$; $V_{SW} = \text{GND or } V_{CC}$	[2] -	5	500	-	5000	μA

Table 6. Static characteristics ...continued

At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
C _I	input capacitance		-	12.5	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance		-	8.0	-	-	-	pF
C _{S(ON)}	ON-state capacitance		-	14.0	-	-	-	pF

- [1] All typical values are measured at T_{amb} = 25 °C.
- [2] These typical values are measured at V_{CC} = 3.3 V.

9.1 Test circuits

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V_I = V_{CC} or GND and V_O = GND or V_{CC}.

Fig 6. Test circuit for measuring OFF-state leakage current

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V_I = V_{CC} or GND and V_O = open circuit.

Fig 7. Test circuit for measuring ON-state leakage current

9.2 ON resistance

Table 7. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see [Figure 9](#) to [Figure 14](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
R _{ON(peak)}	ON resistance (peak)	V _I = GND to V _{CC} ; see Figure 8						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	34.0	130	-	195	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	12.0	30	-	45	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	10.4	25	-	38	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	7.8	20	-	30	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	6.2	15	-	23	Ω

Table 7. ON resistance ...continued

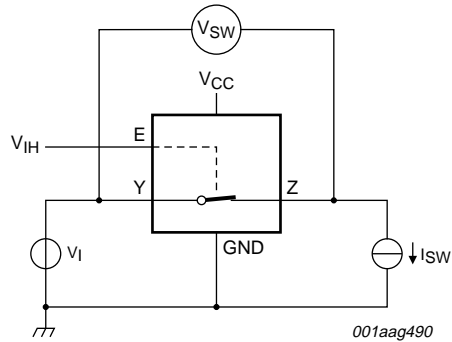
At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see [Figure 9](#) to [Figure 14](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
R _{ON(rail)}	ON resistance (rail)	V _I = GND; see Figure 8						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	8.2	18	-	27	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	7.1	16	-	24	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	6.9	14	-	21	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	6.5	12	-	18	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	5.8	10	-	15	Ω
		V _I = V _{CC} ; see Figure 8						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	10.4	30	-	45	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	7.6	20	-	30	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	7.0	18	-	27	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	6.1	15	-	23	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	4.9	10	-	15	Ω
R _{ON(flat)}	ON resistance (flatness)	V _I = GND to V _{CC} ^[2]						
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	26.0	-	-	-	Ω
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	5.0	-	-	-	Ω
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	3.5	-	-	-	Ω
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	2.0	-	-	-	Ω
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	1.5	-	-	-	Ω

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

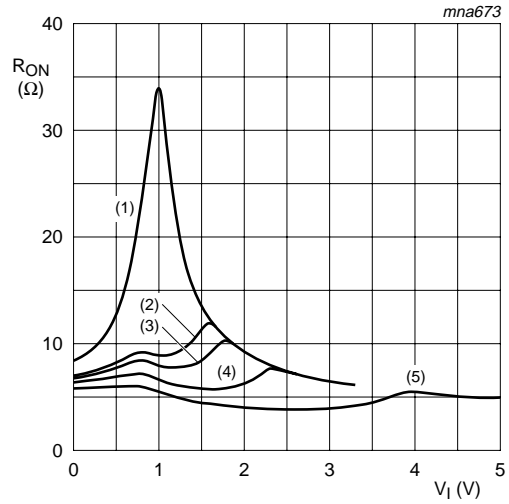
[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

9.3 ON resistance test circuit and graphs



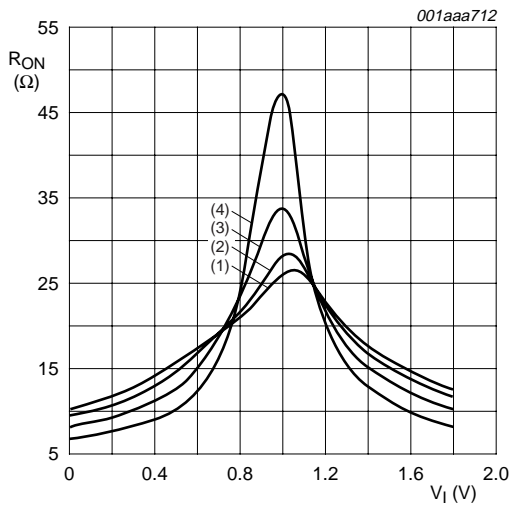
$$R_{ON} = V_{SW} / I_{SW}$$

Fig 8. Test circuit for measuring ON resistance



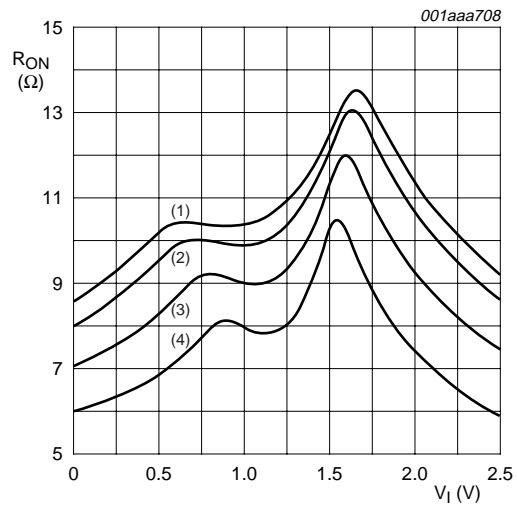
- (1) $V_{CC} = 1.8\text{ V}$.
- (2) $V_{CC} = 2.5\text{ V}$.
- (3) $V_{CC} = 2.7\text{ V}$.
- (4) $V_{CC} = 3.3\text{ V}$.
- (5) $V_{CC} = 5.0\text{ V}$.

Fig 9. Typical ON resistance as a function of input voltage; $T_{amb} = 25\text{ }^{\circ}\text{C}$



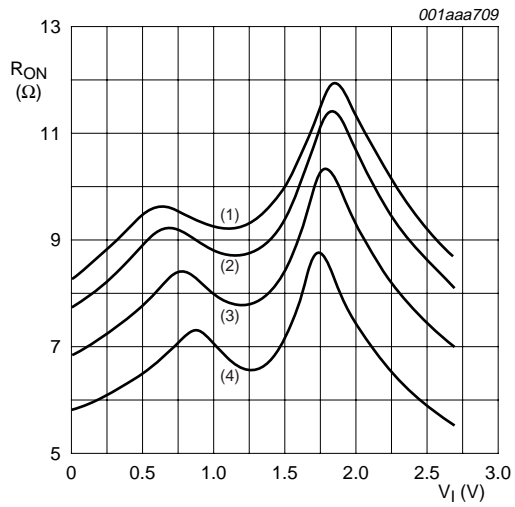
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}$.

Fig 10. ON resistance as a function of input voltage; $V_{CC} = 1.8\text{ V}$



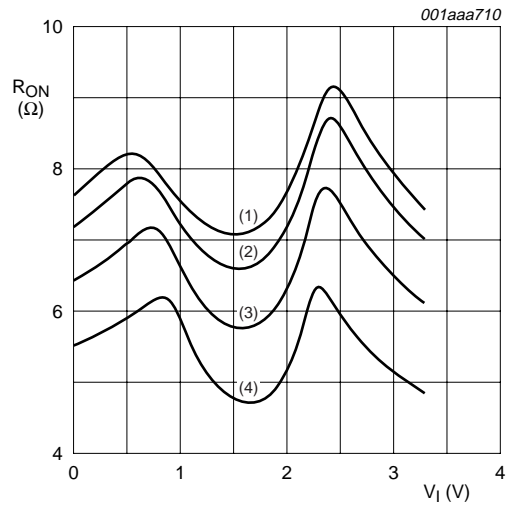
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}$.

Fig 11. ON resistance as a function of input voltage; $V_{CC} = 2.5\text{ V}$



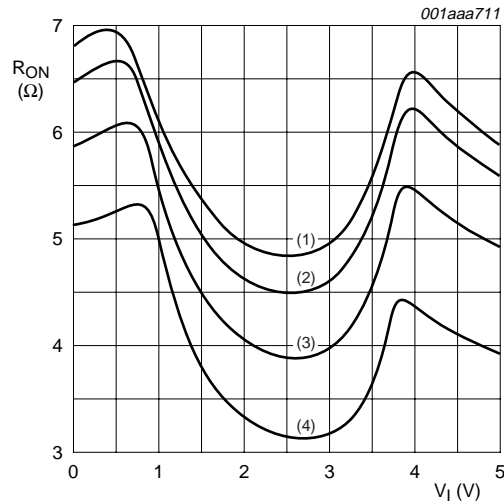
- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85$ °C.
- (3) $T_{amb} = 25$ °C.
- (4) $T_{amb} = -40$ °C.

Fig 12. ON resistance as a function of input voltage; $V_{CC} = 2.7$ V



- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85$ °C.
- (3) $T_{amb} = 25$ °C.
- (4) $T_{amb} = -40$ °C.

Fig 13. ON resistance as a function of input voltage; $V_{CC} = 3.3$ V



- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85$ °C.
- (3) $T_{amb} = 25$ °C.
- (4) $T_{amb} = -40$ °C.

Fig 14. ON resistance as a function of input voltage; $V_{CC} = 5.0$ V

10. Dynamic characteristics

Table 8. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit [Figure 17](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nY to nZ or nZ to nY; see Figure 15 ^{[2][3]}						
		V _{CC} = 1.65 V to 1.95 V	-	0.8	2.0	-	3.0	ns
		V _{CC} = 2.3 V to 2.7 V	-	0.4	1.2	-	2.0	ns
		V _{CC} = 2.7 V	-	0.4	1.0	-	1.5	ns
		V _{CC} = 3.0 V to 3.6 V	-	0.3	0.8	-	1.5	ns
		V _{CC} = 4.5 V to 5.5 V	-	0.2	0.6	-	1.0	ns
t _{en}	enable time	nE to nY or nZ; see Figure 16 ^[4]						
		V _{CC} = 1.65 V to 1.95 V	1.0	5.3	10	1.0	12.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	3.0	5.6	1.0	7.0	ns
		V _{CC} = 2.7 V	1.0	2.6	5.0	1.0	6.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.5	4.4	1.0	5.5	ns
		V _{CC} = 4.5 V to 5.5 V	1.0	1.9	3.9	1.0	5.0	ns
t _{dis}	disable time	nE to nY or nZ; see Figure 16 ^[5]						
		V _{CC} = 1.65 V to 1.95 V	1.0	4.2	9.0	1.0	11.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	2.4	5.5	1.0	7.0	ns
		V _{CC} = 2.7 V	1.0	3.6	6.5	1.0	8.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	3.4	6.0	1.0	7.5	ns
		V _{CC} = 4.5 V to 5.5 V	1.0	2.5	5.0	1.0	6.5	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f _i = 10 MHz; V _I = GND to V _{CC} ^[6]						
		V _{CC} = 2.5 V	-	11.0	-	-	-	pF
		V _{CC} = 3.3 V	-	12.5	-	-	-	pF
		V _{CC} = 5.0 V	-	15.6	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).

[4] t_{en} is the same as t_{PZH} and t_{PZL}.

[5] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum \{(C_L + C_{S(ON)}) \times V_{CC}^2 \times f_o\} \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

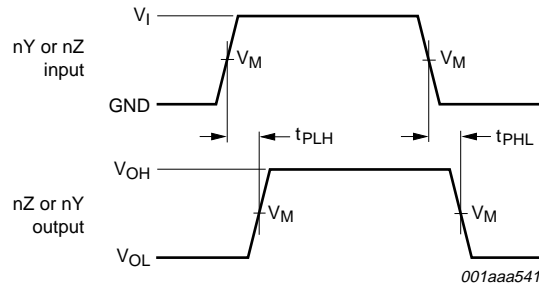
C_{S(ON)} = maximum ON-state switch capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

∑{(C_L + C_{S(ON)}) × V_{CC}² × f_o} = sum of the outputs.

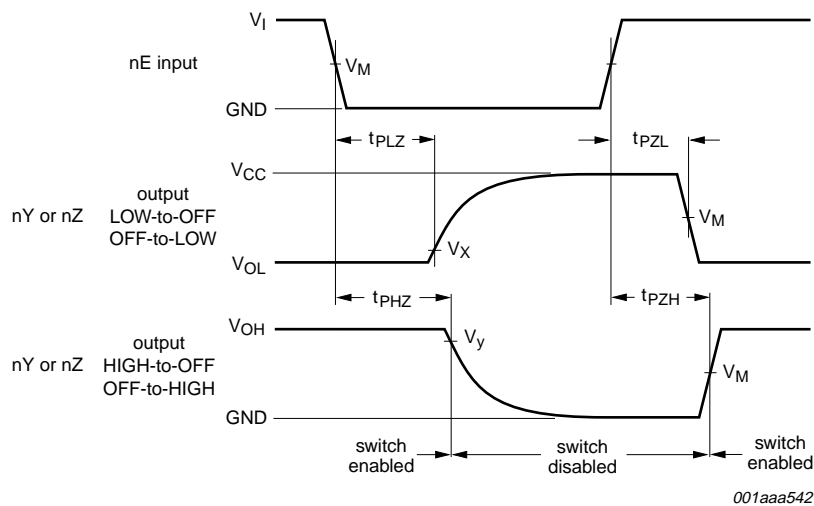
10.1 Waveforms and test circuit



Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 15. Input (nY or nZ) to output (nZ or nY) propagation delays



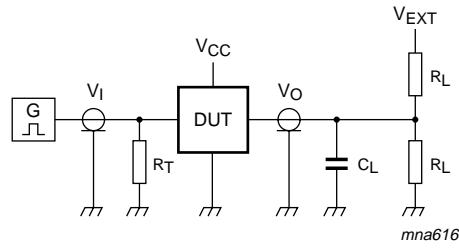
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 16. Enable and disable times

Table 9. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
1.65 V to 1.95 V	$0.5V_{CC}$	$0.5 V_{CC}$	$V_{OL} + 0.15 V$	$V_{OH} - 0.15 V$
2.3 V to 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.15 V$	$V_{OH} - 0.15 V$
2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
3.0 V to 3.6 V	1.5 V	1.5 V	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
4.5 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$



Test data is given in [Table 10](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

V_{EXT} = External voltage for measuring switching times.

Fig 17. Load circuit for switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open	GND	$2V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	GND	$2V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2V_{CC}$

10.2 Additional dynamic characteristics

Table 11. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = 25^\circ C$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	$R_L = 10$ k Ω ; $C_L = 50$ pF; $f_i = 1$ kHz; see Figure 18				
		$V_{CC} = 1.65$ V	-	0.032	-	%
		$V_{CC} = 2.3$ V	-	0.008	-	%
		$V_{CC} = 3$ V	-	0.006	-	%
		$V_{CC} = 4.5$ V	-	0.005	-	%
		$R_L = 10$ k Ω ; $C_L = 50$ pF; $f_i = 10$ kHz; see Figure 18				
		$V_{CC} = 1.65$ V	-	0.068	-	%
		$V_{CC} = 2.3$ V	-	0.009	-	%
		$V_{CC} = 3$ V	-	0.008	-	%
		$V_{CC} = 4.5$ V	-	0.006	-	%

Table 11. Additional dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = 25\text{ }^{\circ}\text{C}$.

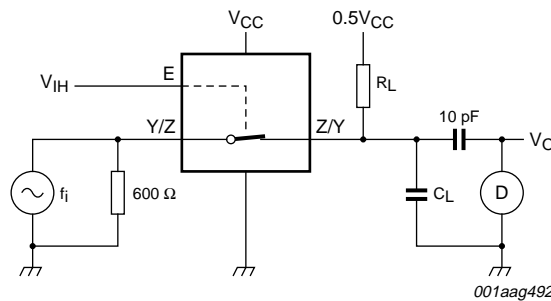
Symbol	Parameter	Conditions	Min	Typ	Max	Unit		
$f_{(-3\text{dB})}$	-3 dB frequency response	$R_L = 600\ \Omega$; $C_L = 50\ \text{pF}$; see Figure 19						
		$V_{CC} = 1.65\ \text{V}$	-	170	-	MHz		
		$V_{CC} = 2.3\ \text{V}$	-	210	-	MHz		
		$V_{CC} = 3\ \text{V}$	-	212	-	MHz		
		$V_{CC} = 4.5\ \text{V}$	-	215	-	MHz		
		$R_L = 50\ \Omega$; $C_L = 5\ \text{pF}$; see Figure 19						
		$V_{CC} = 1.65\ \text{V}$	-	> 500	-	MHz		
		$V_{CC} = 2.3\ \text{V}$	-	> 500	-	MHz		
		$V_{CC} = 3\ \text{V}$	-	> 500	-	MHz		
		$V_{CC} = 4.5\ \text{V}$	-	> 500	-	MHz		
		α_{iso}	isolation (OFF-state)	$R_L = 600\ \Omega$; $C_L = 50\ \text{pF}$; $f_i = 1\ \text{MHz}$; see Figure 20				
				$V_{CC} = 1.65\ \text{V}$	-	-46	-	dB
$V_{CC} = 2.3\ \text{V}$	-			-46	-	dB		
$V_{CC} = 3\ \text{V}$	-			-46	-	dB		
$V_{CC} = 4.5\ \text{V}$	-			-46	-	dB		
$R_L = 50\ \Omega$; $C_L = 5\ \text{pF}$; $f_i = 1\ \text{MHz}$; see Figure 20								
$V_{CC} = 1.65\ \text{V}$	-			-42	-	dB		
$V_{CC} = 2.3\ \text{V}$	-			-42	-	dB		
$V_{CC} = 3\ \text{V}$	-			-42	-	dB		
$V_{CC} = 4.5\ \text{V}$	-			-42	-	dB		
V_{ct}	crosstalk voltage			between digital inputs and switch; $R_L = 600\ \Omega$; $C_L = 50\ \text{pF}$; $f_i = 1\ \text{MHz}$; $t_r = t_f = 2\ \text{ns}$; see Figure 21				
				$V_{CC} = 1.65\ \text{V}$	-	69	-	mV
		$V_{CC} = 2.3\ \text{V}$	-	87	-	mV		
		$V_{CC} = 3\ \text{V}$	-	156	-	mV		
		$V_{CC} = 4.5\ \text{V}$	-	302	-	mV		
Xtalk	crosstalk	between switches; $R_L = 600\ \Omega$; $C_L = 50\ \text{pF}$; $f_i = 1\ \text{MHz}$; see Figure 22						
		$V_{CC} = 1.65\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 2.3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 4.5\ \text{V}$	-	-58	-	dB		
		between switches; $R_L = 50\ \Omega$; $C_L = 5\ \text{pF}$; $f_i = 1\ \text{MHz}$; see Figure 22						
		$V_{CC} = 1.65\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 2.3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 4.5\ \text{V}$	-	-58	-	dB		

Table 11. Additional dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Q_{inj}	charge injection	$C_L = 0.1\text{ nF}$; $V_{gen} = 0\text{ V}$; $R_{gen} = 0\text{ }\Omega$; $f_i = 1\text{ MHz}$; $R_L = 1\text{ M}\Omega$; see Figure 23				
		$V_{CC} = 1.8\text{ V}$	-	3.3	-	pC
		$V_{CC} = 2.5\text{ V}$	-	4.1	-	pC
		$V_{CC} = 3.3\text{ V}$	-	5.0	-	pC
		$V_{CC} = 4.5\text{ V}$	-	6.4	-	pC
		$V_{CC} = 5.5\text{ V}$	-	7.5	-	pC

10.2.1 Test circuits



Test conditions:

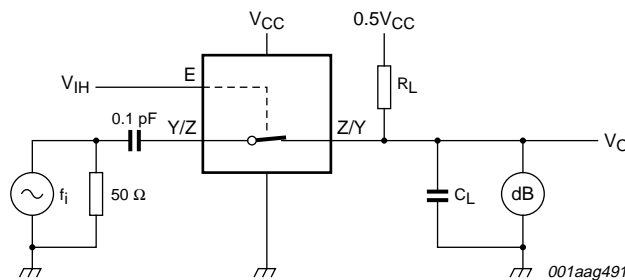
$V_{CC} = 1.65\text{ V}$: $V_i = 1.4\text{ V}$ (p-p).

$V_{CC} = 2.3\text{ V}$: $V_i = 2\text{ V}$ (p-p).

$V_{CC} = 3\text{ V}$: $V_i = 2.5\text{ V}$ (p-p).

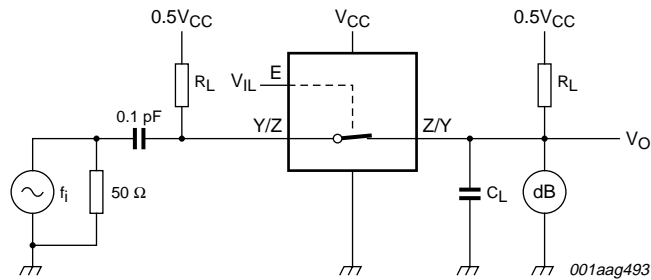
$V_{CC} = 4.5\text{ V}$: $V_i = 4\text{ V}$ (p-p).

Fig 18. Test circuit for measuring total harmonic distortion



Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads -3 dB.

Fig 19. Test circuit for measuring the frequency response when switch is in ON-state



Adjust f_i voltage to obtain 0 dBm level at input.

Fig 20. Test circuit for measuring isolation (OFF-state)

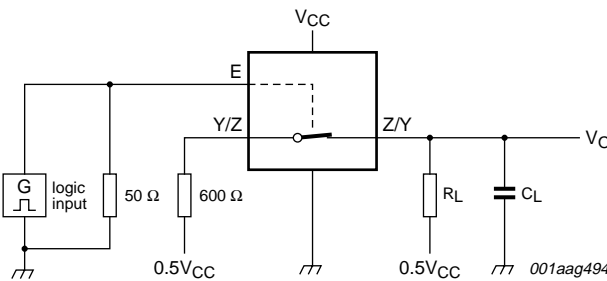
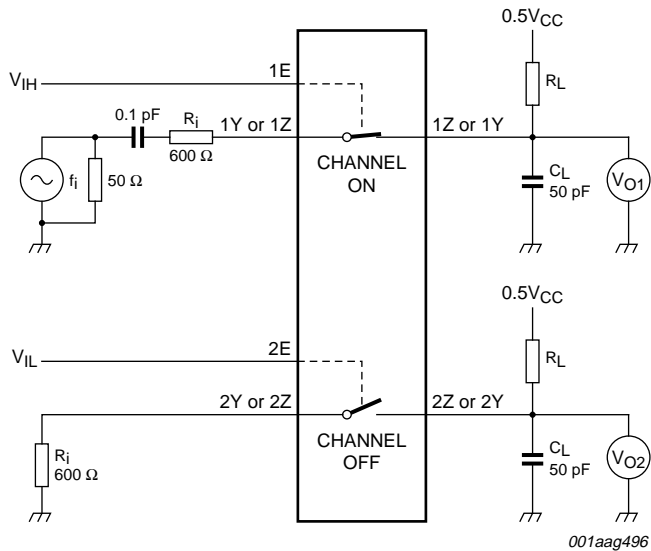
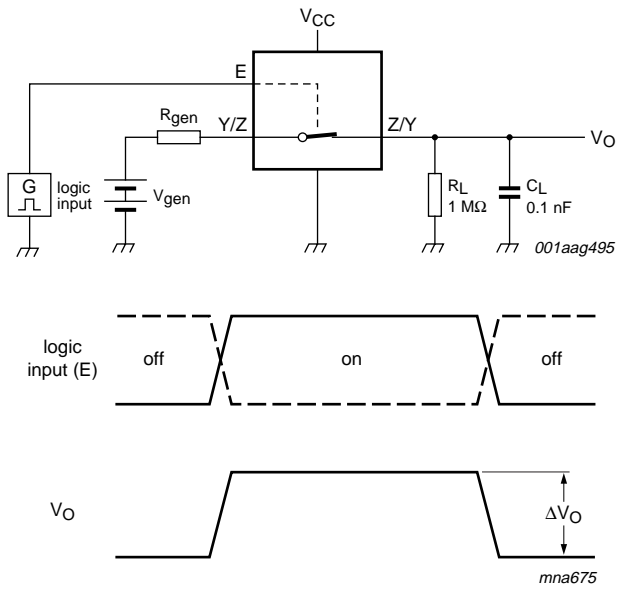


Fig 21. Test circuit for measuring crosstalk voltage (between digital inputs and switch)



$20 \log_{10} (V_{O2} / V_{O1})$ or $20 \log_{10} (V_{O1} / V_{O2})$.

Fig 22. Test circuit for measuring crosstalk between switches



$$Q_{inj} = \Delta V_O \times C_L$$

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 23. Test circuit for measuring charge injection

11. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

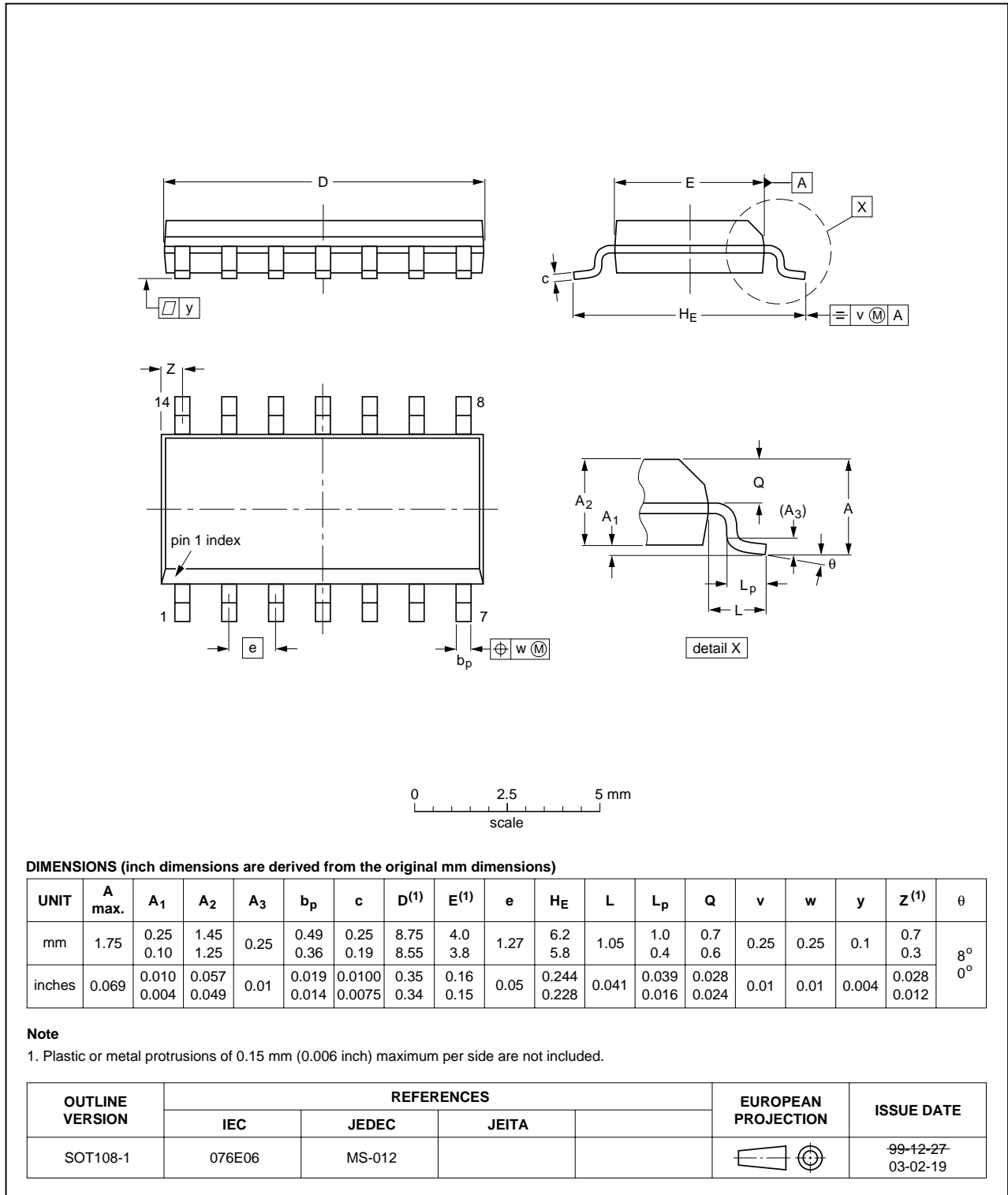


Fig 24. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

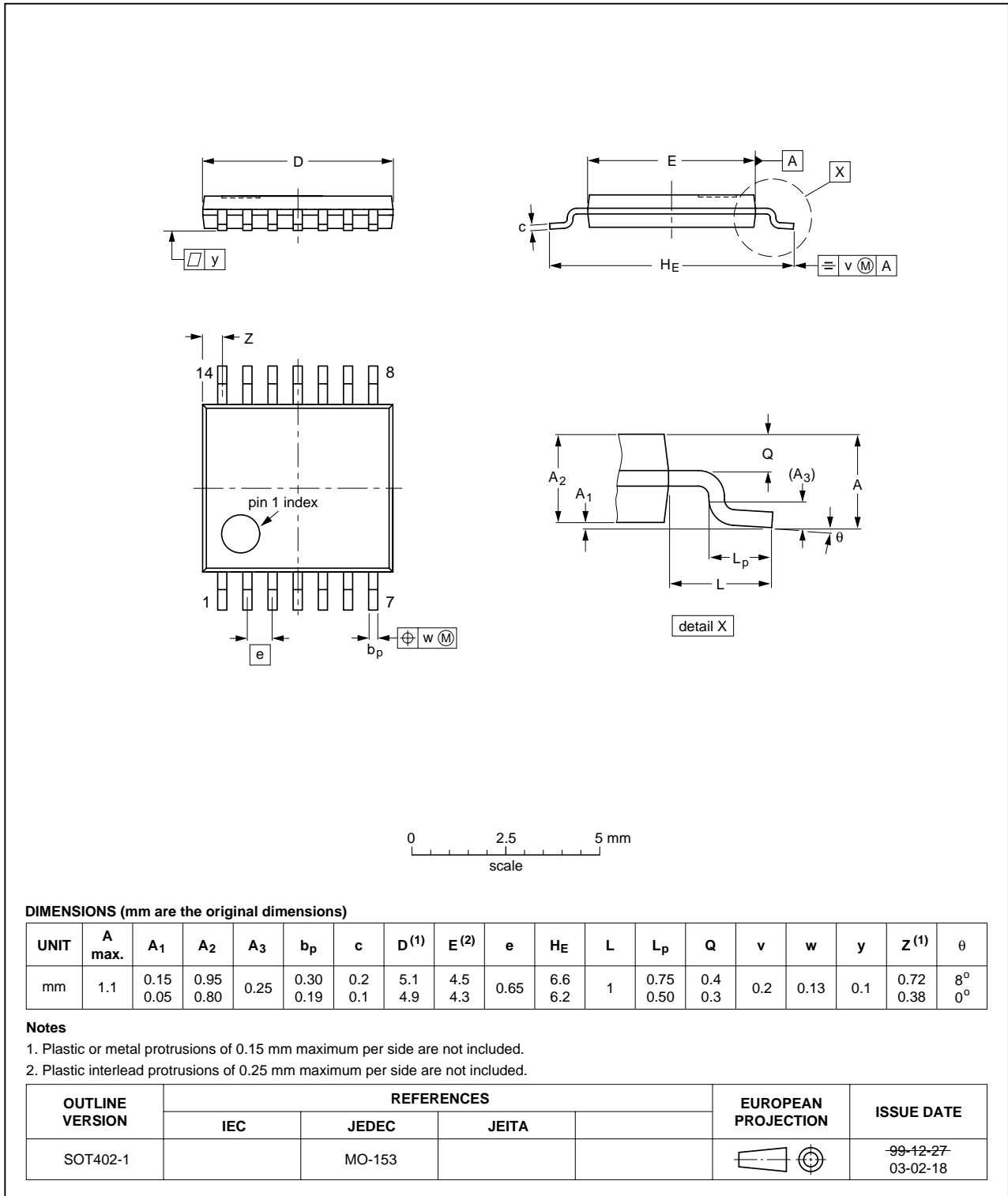


Fig 25. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

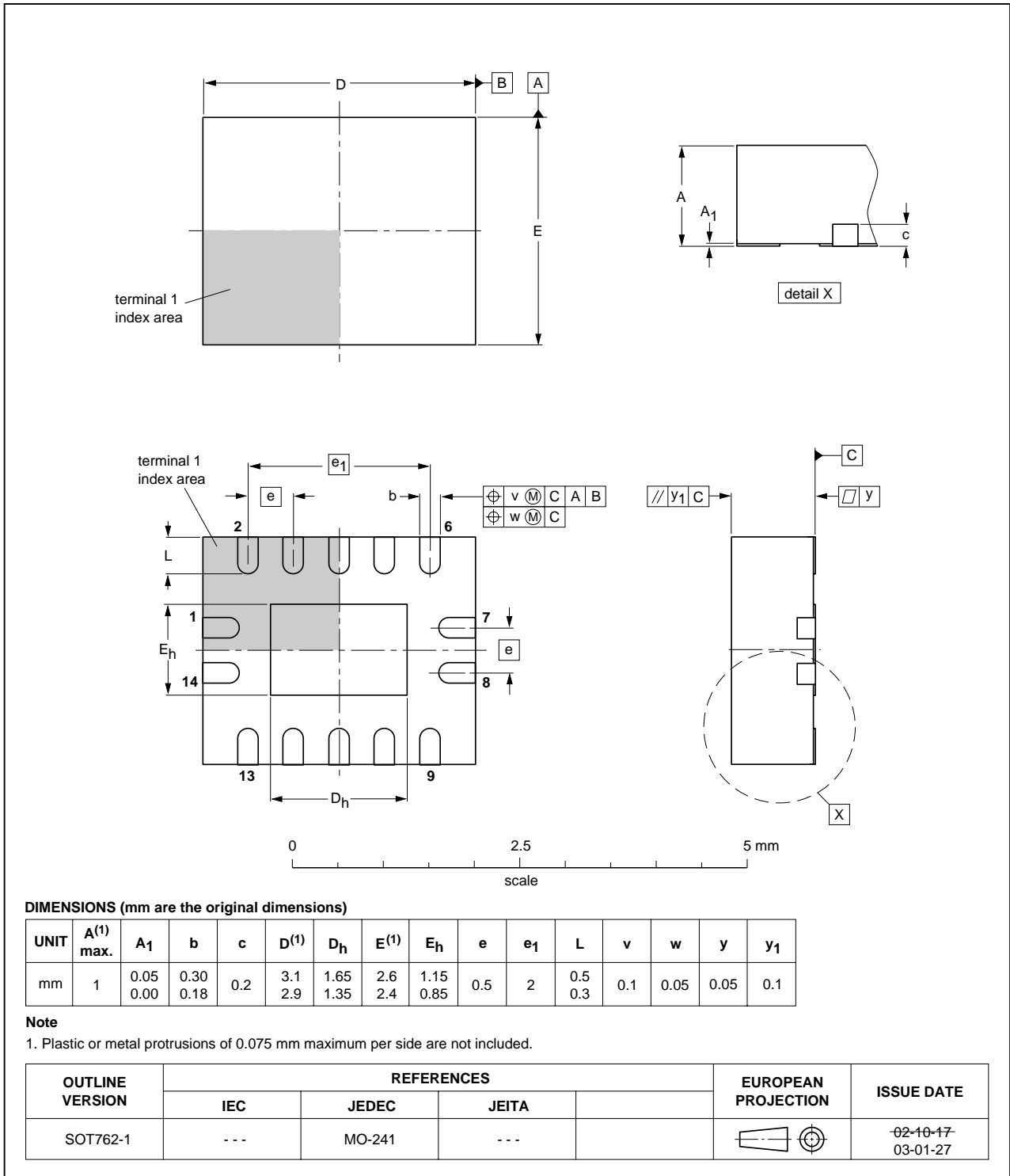


Fig 26. Package outline SOT762-1 (DHVQFN14)

12. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

13. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC4066_2	20070827	Product data sheet	-	74LVC4066_1
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Section 2 “Features”: <ul style="list-style-type: none"> Added: Wide supply voltage range from 1.65 V to 5.5 V Added: Switch handling capability of 32 mA Added: Multiple package options Deleted: Complies with JEDESD-8 standards Added: Specified from –40 °C to +85 °C and –40 °C to +125 °C Added: Enable input accepts voltages up to 5 V Section 7 “Limiting values” <ul style="list-style-type: none"> Added: Derating factors of the applicable packages Section 9 “Static characteristics” <ul style="list-style-type: none"> Changed: Maximum values of ON resistance (peak) parameters and graphics. Section 10 “Dynamic characteristics”: <ul style="list-style-type: none"> Changed: Typical values of the charge injection. 			
74LVC4066_1	20030812	Product specification	-	-

14. Legal information

14.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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